High-temperature phosphorous passivation of Si surface for improved heteroepitaxial growth of InAs as an initial step of III-As MOVPE on Si

Momoko Deura, Yoshiyuki Kondo, Mitsuru Takenaka, Shinichi Takagi, Yukihiro Shimogaki, Yoshiaki Nakano and Masakazu Sugiyama

School of Engineering, The University of Tokyo, 2-11-16 Yayoi, Bunkyo-ku, Tokyo 113-8656, Japan
Phone: +81-3-5841-6753, Fax: +81-3-5841-6027, E-mail: deura@ee.t.u-tokyo.ac.jp


1. Introduction

Most recently, conventional Si large scale integrated circuits (LSIs) greatly require III-V compound semiconductors for the channel layer of transistors and light source to enhance their performance itself or improve new functions. For this integration of III-V semiconductors on Si, we have proposed micro-channel selective-area growth (MC-SAG) [1] to overcome huge difference in lattice constants, and InGaAs growth has been studied using metal-organic vapor phase epitaxy (MOVPE). However, not InGaAs but InAs is suitable for obtaining a single nucleus of a III-V layer on Si. Moreover, in the case of MOVPE, the surface has to be protected from contamination inside a reactor. We have found that phosphorous treatment of Si, rather than arsenic, in an MOVPE reactor at the growth temperature is effective to promote uniform InAs nucleation on Si [3]. However, we have not yet achieved complete coverage of a Si growth area with an InAs flat island, which is desired to promote succeeding single-grain InGaAs growth with high uniformity. In this study, we tried higher temperature pretreatment than the growth temperature of 610°C during heating up and shut off below 400°C during cooling. We measured X-ray photoelectron spectroscopy (XPS) and analyzed elements existing on the Si surfaces which had been annealed in three kinds of ambient: only H2, TBAs and TBP.

3. Results and discussion

Surface state of Si after annealing

Figure 1 shows the atomic ratios of deposited elements on Si surfaces annealed in H2, TBAs and TBP ambient, respectively. The values on the surface just transferred into N2-purged glovebox attached to the MOVPE apparatus are also shown for reference. In addition to Si, C and O peaks, P peak was observed on the non-annealed surface due to contamination inside the glovebox. For the H2- and TBAs-annealed surfaces, P can be contaminated also during annealing.

In the case of the H2-annealed surface, trace amount of As, Ga and In were also observed due to the reactor contamination because these elements are frequently used in our reactor. A large amount of C was also observed, probably due to adsorbed reaction by-products on the surface of a reactor. This carbon contamination of the Si surface was reduced to the background level for the TBP- and TBAs-annealed surfaces, suggesting surface passivation of Si with

![Fig. 1](image-url) Atomic ratios of six elements versus Si on Si surfaces annealed in H2, TBAs and TBP ambient measured by X-ray photoelectron spectroscopy (XPS). The values on the surface just transferred into N2-purged box are also shown for reference. X-ray source of XPS was Al Kα (1453.6 eV) and the take-off angle was 45°. These values were calculated from areas for each XPS peak corrected by the sensitivity factors.
group-V atoms is effective to prevent the surface contamination.

In the case of the TBAs-annealed surface, however, fraction of O was significantly larger than other surfaces. This is in contrast to the TBP-annealed surface, for which only a small amount of O atoms was observed. It is possible that TBAs-annealed Si surface is imperfectly covered with As. Uncovered fraction Si of surface was easily oxidized. Affinity between As and O probably promoted surface oxidation. This finding suggests that As is not suitable for surface passivation of Si, even when we want to grow III-arsenide layer on Si surface.

On the other hand, the TBP-treated surface was not oxidized significantly. This is probably because P atoms passivated Si surface completely at high temperature. In this sense, not As but P is suitable for surface passivation of Si prior to the growth of a III-arsenide layer. However, excessive high temperature promotes bond formation between surface P and Ga atoms which desorbed from inside of the reactor.

InAs growth after annealing

Figures 2 and 3 are the bird’s-eye view scanning electron microscopy (SEM) pictures and 2θ-ω peaks of X-ray diffraction (XRD) from the (111) plane for InAs islands grown in 5 minutes after annealing in H$_2$, TBAs and TBP ambient as stated above.

Most of InAs islands on the H$_2$-annealed Si surface were grown laterally and buried Si growth areas, the shape of which were uniform. However, the number of islands which were grown incoherently was higher than those on substrates annealed in other ambient and plural nuclei were observed in some growth areas. XRD peak for InAs shown in Fig. 3 is also significantly broad, indicating the poor crystallinity. This poor crystallinity can be due to rough surface of these islands. Another possibility is that small plural nuclei were generated using a lot of contamination as a core and they were coalesced to a good-looking hexagonal island, i.e., a multi-domain island.

On the other hand, the uniformity of the shape of InAs islands on TBAs-annealed Si was poor and Si surface was not buried by InAs although the XRD peak was sharp. In addition, nuclei did not emerge in some growth area. This non-uniformity of the shape or poor nucleation reflects the imperfect coverage of As atoms and the partial oxidation on Si surfaces.

In contrast, InAs islands on TBP-annealed Si were nucleated perfectly and most of them were grown laterally; the height of islands was smallest. Sharp XRD peak in Fig. 3 indicates the high coherency of islands. However, the shape of islands was random, that is, islands did not show the perfect hexagonal shape. This random shape is presumed to be because Ga contamination has an effect on nucleation of InAs or the substitution of P atoms with As atoms at the topmost of Si at the beginning of the growth was not successful.

4. Summary

We investigated the state of Si(111) surface and the effect on InAs growth after annealing at high temperature with and without TBAs or TBP in H$_2$ ambient in the MOVPE reactor. TBP-annealed surface is better in terms of the protection effect of surface contamination, the perfect nucleation and the lateral growth of InAs. However, Ga starts to re-desorb from inside of the reactor and adsorb on P-terminated Si surface at too high temperature, which may affect InAs growth. Accordingly, we should decide the proper annealing temperature to avoid adsorbing contamination on Si surface. Furthermore, we should also investigate how to switch from the flow of TBP to InAs growth, which TBAs is used.

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References